

MA739

Silicon epitaxial planer type

For high-frequency rectification

■ Features

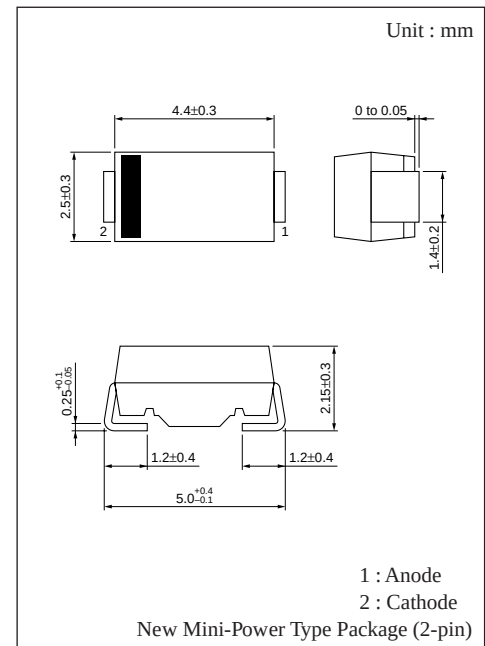
- Forward current (average) $I_{F(AV)}$: 0.7A type
- Reverse voltage (DC value) V_R : 90V
- Automatic insertion possible with emboss taping

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	90	V
Repetitive peak reverse voltage	V_{RRM}	90	V
Average forward current	$I_{F(AV)}^{*1}$	0.7	A
Non-repetitive peak forward surge current	I_{FSM}^{*2}	10	A
Junction temperature	T_j	-140 to +125	°C
Storage temperature	T_{stg}	-140 to +125	°C

*1 With a printed-circuit board

*2 50Hz sine wave, one-cycle wave, high value (non-repetitive)



Marking Symbol : PE

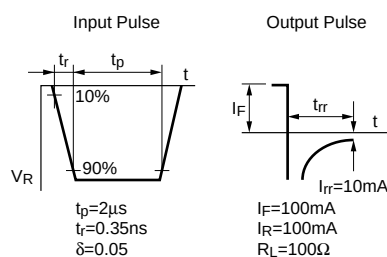
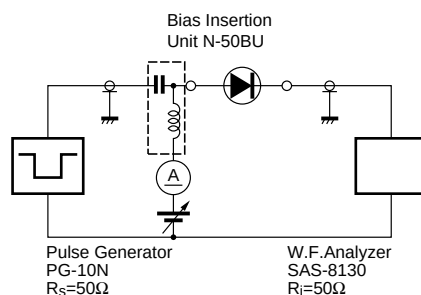
■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 90V$			1	mA
Forward voltage (DC)	V_F	$I_F = 0.7A$			0.8	V
Terminal capacitance	C_t	$V_R = 10V, f = 1MHz$		50		pF
Reverse recovery time	t_{rr}^*	$I_F = I_R = 100mA$ $I_{rr} = 10mA, R_L = 100\Omega$			100	ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

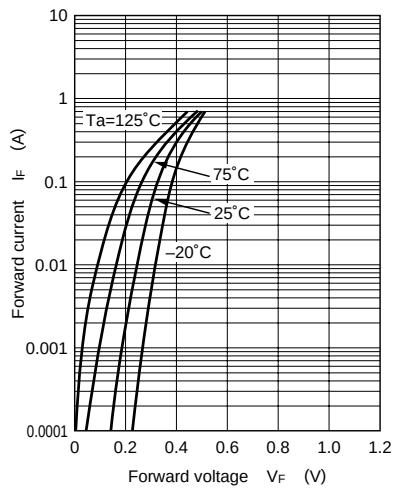
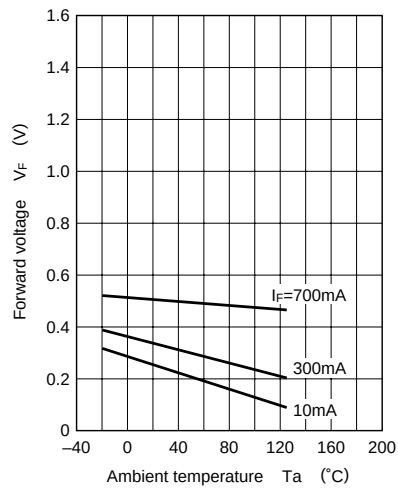
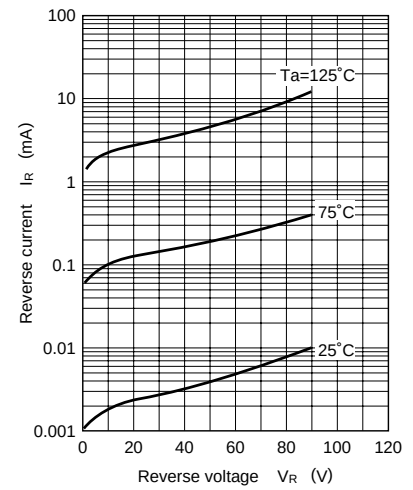
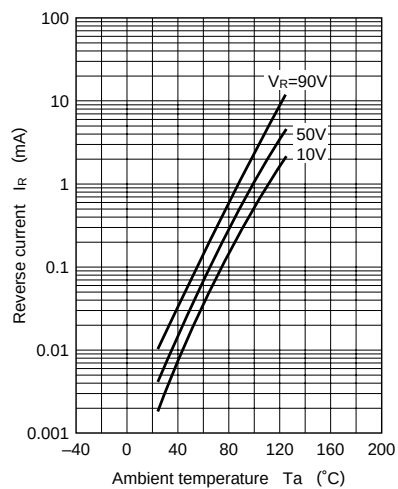
2. Rated input/output frequency : 10MHz

3. * t_{rr} measuring circuit



■ Marking



$I_F - V_F$  $I_F - T_a$  $I_R - V_R$  $I_R - T_a$  $C_t - V_R$ 